
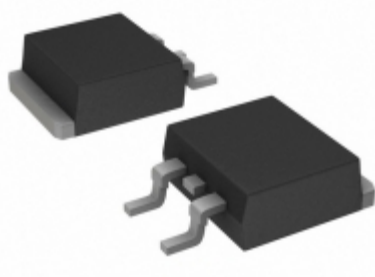








	<h2 style="color: #E67E22;">FQB4N25TM</h2> <p>Hersteller-Teilenummer: FQB4N25TM</p> <p>Hersteller / Marke: Fairchild/ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET N-CH 250V 3.6A D2PAK</p> <p>Datenblätter:  FQB4N25TM.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 32363 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQB4N25TM
Hersteller	Fairchild/ON Semiconductor
Beschreibung	MOSFET N-CH 250V 3.6A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	32363 pcs Stock
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 52W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (V _{dss})	250V
Strom - Ununterbrochener Abfluss (I _d) bei 25 °C	3.6A (Tc)
R _{ds} On (Max) @ I _d , V _{gs}	1.75 Ohm @ 1.8A, 10V
V _{GS} (th) (Max) @ I _d	5V @ 250µA
Gate Charge (Q _g) (Max) @ V _{gs}	5.6nC @ 10V
Eingabekapazität (C _{iss}) (Max) @ V _{ds}	200pF @ 25V
Verpackung	Tape & Reel (TR)






















FQB4N25TM ist neu im Original, Suche FQB4N25TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB4N25TM Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB4N25TM: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQB4N20TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 3.6A D2PAK</p>	 <p>FQB4N20TM VB FQB4N20TM VB</p>	 <p>FQB4N25TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 250V 3.6A D2PAK</p>	 <p>FQB4N20LTM Fairchild/ON Semiconductor MOSFET N-CH 200V 3.8A D2PAK</p>
 <p>FQB4N20TM Fairchild/ON Semiconductor MOSFET N-CH 200V 3.6A D2PAK</p>	 <p>FQB4N50TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 500V 3.4A D2PAK</p>	 <p>FQB4N50TM Fairchild/ON Semiconductor MOSFET N-CH 500V 3.4A D2PAK</p>	 <p>FQB4N60 Fairchild/ON Semiconductor FQB4N60 FAIRCHILD</p>

heiße Teile

Mehr

 FQB3N30TM	 FQB3N40TM	 FQB3N40TM	 FQB3N60C	 FQB3N80TM
 FQB3N80TM	 FQB3N90TM	 FQB3N90TM	 FQB3P20TM	 FQB3P20TM
 FQB3P50TM	 FQB3P50TM	 FQB44N10	 FQB44N10TM	 FQB44N10TM
 FQB46N15	 FQB46N15TM	 FQB47P06	 FQB47P06TM	 FQB4N20L
 FQB4N20LTM	 FQB4N20LTM	 FQB4N20TM	 FQB4N20TM	 FQB4N25TM
 FQB4N20TM	 FQB4N50TM	 FQB4N50TM	 FQB4N60C	 FQB4N80TM
 FQB4N80TM	 FQB4N90TM	 FQB4N90TM	 FQB4P25TM	 FQB4P25TM
 FQB50N03	 FQB50N06	 FQB50N06C	 FQB50N06L	 FQB50N06LTM
 FQB50N06LTM	 FQB50N06M	 FQB50N06TM	 FQB50N06TM	 FQB50N06TM-NL
 FQB55N06TM	 FQB55N06TM	 FQB55N10	 FQB55N10TM	 FQB55N10TM

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